ABSTRACT OF THE DISCLOSURE

A photoelectric conversion device capable of improving an open-circuit voltage is obtained. In this photoelectric conversion device, many of crystal grains contained in a third non-single-crystalline semiconductor layer have major axes substantially perpendicular to a main surface of a substrate on an interfacial portion between at least either a first non-single-crystalline semiconductor layer or a second non-single-crystalline semiconductor layer and the third non-single-crystalline semiconductor layer, and many of crystal grains contained in either semiconductor layer have major axes substantially parallel to the main surface of the substrate on the aforementioned interfacial portion.